



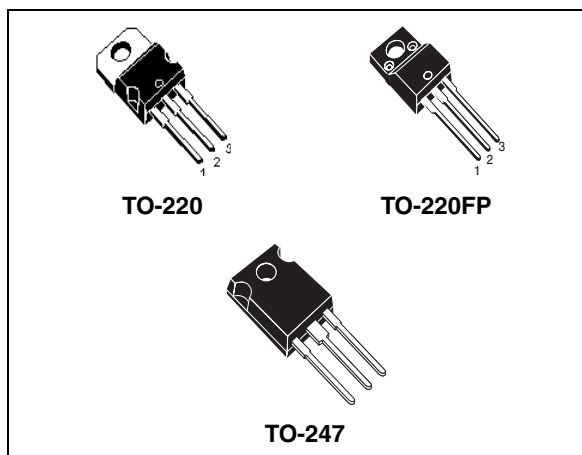
STP5NK100Z - STF5NK100Z STW5NK100Z

N-channel 1000V - 2.7Ω - 3.5A - TO-220/TO-220FP/TO-247
Zener-protected SuperMESH™ Power MOSFET

General features

| Type | V _{DSS} (@T _{jmax}) | R _{DS(on)} | I _D |
|------------|---|---------------------|----------------|
| STF5NK100Z | 1000 V | < 3.7 Ω | 3.5 A |
| STP5NK100Z | 1000 V | < 3.7 Ω | 3.5 A |
| STW5NK100Z | 1000 V | < 3.7 Ω | 3.5 A |

- Extremely high dv/dt capability
- 100% avalanche tested
- Gate charge minimized
- Very low intrinsic capacitances
- Very good manufacturing repeatability



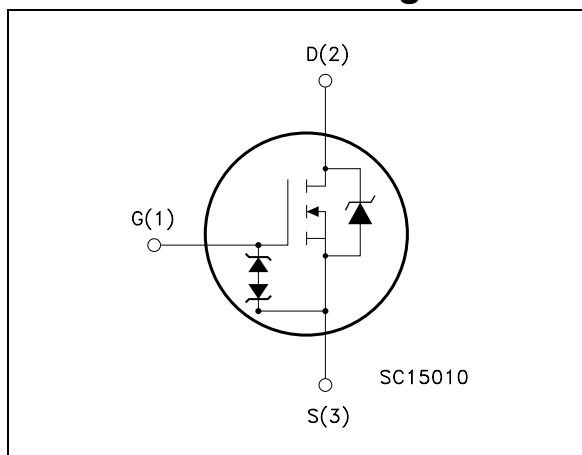
Description

The SuperMESH™ series is obtained through an extreme optimization of ST's well established stripbased PowerMESH™ layout. In addition to pushing on-resistance significantly down, special care is taken to ensure a very good dv/dt capability for the most demanding applications. Such series complements ST full range of high voltage MOSFETs including revolutionary MDmesh™ products.

Applications

- Switching application

Internal schematic diagram



Order codes

| Part number | Marking | Package | Packaging |
|-------------|----------|----------|-----------|
| STF5NK100Z | F5NK100Z | TO-220FP | Tube |
| STP5NK100Z | P5NK100Z | TO-220 | Tube |
| STW5NK100Z | W5NK100Z | TO-247 | Tube |

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1 Electrical ratings

Table 1. Absolute maximum ratings

| Symbol | Parameter | Value | | Unit |
|--------------------|---|---------------|--------------------|---------------------|
| | | TO-220/TO-247 | TO-220FP | |
| V_{DS} | Drain-source voltage ($V_{GS} = 0$) | 1000 | | V |
| V_{GS} | Gate-source voltage | ± 30 | | V |
| I_D | Drain current (continuous) at $T_C = 25^\circ\text{C}$ | 3.5 | 3.5 ⁽¹⁾ | A |
| I_D | Drain current (continuous) at $T_C = 100^\circ\text{C}$ | 2.2 | 2.2 ⁽¹⁾ | A |
| $I_{DM}^{(2)}$ | Drain current (pulsed) | 14 | 14 ⁽¹⁾ | A |
| P_{TOT} | Total dissipation at $T_C = 25^\circ\text{C}$ | 125 | 30 | W |
| | Derating factor | 1 | 0.24 | W/ $^\circ\text{C}$ |
| $V_{ESD(G-S)}$ | Gate source ESD (HBM-C=100pF, R=1.5K Ω) | 4000 | | V |
| $dv/dt^{(3)}$ | Peak diode recovery voltage slope | 4.5 | | V/ns |
| V_{ISO} | Insulation withstand voltage (RMS) from all three leads to external heat sink ($t=1\text{s}$; $T_c=25^\circ\text{C}$) | - | 2500 | V |
| T_J T_{stg} | Operating junction temperature Storage temperature | -55 to 150 | | $^\circ\text{C}$ |

1. Limited only by maximum temperature allowed
2. Pulse width limited by safe operating area
3. $I_{SD} \leq 3.5\text{A}$, $di/dt \leq 200\text{A}/\mu\text{s}$, $V_{DD} \leq V_{(BR)DSS}$, $T_j \leq T_{JMAX}$.

Table 2. Thermal data

| Symbol | Parameter | Value | | Unit |
|----------------|--|------------------|----------|---------------------------|
| | | TO-220 TO-247 | TO-220FP | |
| $R_{thj-case}$ | Thermal resistance junction-case max | 1 | 4.2 | $^\circ\text{C}/\text{W}$ |
| R_{thj-a} | Thermal resistance junction-ambient max | 62.5 | | $^\circ\text{C}/\text{W}$ |
| T_l | Maximum lead temperature for soldering purpose | 300 | | $^\circ\text{C}$ |

Table 3. Avalanche characteristics

| Symbol | Parameter | Value | Unit |
|----------|---|-------|------|
| I_{AR} | Avalanche current, repetitive or not-repetitive (pulse width limited by T_j Max) | 3.5 | A |
| E_{AS} | Single pulse avalanche energy (starting $T_j=25^\circ\text{C}$, $I_d=I_{AR}$, $V_{DD}=50\text{V}$) | 250 | mJ |

Table 4. Gate-source zener diode

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|------------|-------------------------------|--------------------------------------|------|------|------|------|
| BV_{GSO} | Gate-source breakdown voltage | $I_{GS}=\pm 1\text{mA}$ (open drain) | 30 | | | V |

1.1 Protection features of gate-to-source zener diodes

The built-in back-to-back Zener diodes have specifically been designed to enhance not only the device's ESD capability, but also to make them safely absorb possible voltage transients that may occasionally be applied from gate to source. In this respect the Zener voltage is appropriate to achieve an efficient and cost-effective intervention to protect the device's integrity. These integrated Zener diodes thus avoid the usage of external components.

2 Electrical characteristics

($T_{CASE}=25^{\circ}C$ unless otherwise specified)

Table 5. On/off states

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|---------------|--|--|------|------|----------|--------------------|
| $V_{(BR)DSS}$ | Drain-source breakdown voltage | $I_D = 1mA, V_{GS} = 0$ | 1000 | | | V |
| I_{DSS} | Zero gate voltage drain current ($V_{GS} = 0$) | $V_{DS} = \text{Max rating},$ $V_{DS} = \text{Max rating},$ $T_c = 125^{\circ}C$ | | | 1 50 | μA μA |
| I_{GSS} | Gate body leakage current ($V_{GS} = 0$) | $V_{GS} = \pm 20V$ | | | ± 10 | μA |
| $V_{GS(th)}$ | Gate threshold voltage | $V_{DS} = V_{GS}, I_D = 100\mu A$ | 3 | 3.75 | 4.5 | V |
| $R_{DS(on)}$ | Static drain-source on resistance | $V_{GS} = 10V, I_D = 1.75 A$ | | 2.7 | 3.7 | Ω |

Table 6. Dynamic

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|-------------------|-------------------------------|--|------|------|------|------|
| $g_{fs}^{(1)}$ | Forward transconductance | $V_{DS} = 15V, I_D = 1.75A$ | | 4 | | S |
| C_{iss} | Input capacitance | $V_{DS} = 25V, f = 1 \text{ MHz}, V_{GS} = 0$ | | 1154 | | pF |
| C_{oss} | Output capacitance | | | 106 | | pF |
| C_{rss} | Reverse transfer capacitance | | | 21.3 | | pF |
| $C_{osseq}^{(2)}$ | Equivalent output capacitance | $V_{GS} = 0, V_{DS} = 0V \text{ to } 800V$ | | 46.8 | | pF |
| $t_{d(on)}$ | Turn-on delay time | $V_{DD} = 500V, I_D = 1.75A,$ $R_G = 4.7\Omega, V_{GS} = 10V$ (see Figure 20) | | 22.5 | | ns |
| t_r | Rise time | | | 7.7 | | ns |
| $t_{d(off)}$ | Off-voltage rise time | | | 51.5 | | ns |
| t_f | Fall time | | | 19 | | ns |
| Q_g | Total gate charge | $V_{DD} = 800V, I_D = 3.5A$ $V_{GS} = 10V$ (see Figure 21) | | 42 | | nC |
| Q_{gs} | Gate-source charge | | | 7.3 | 59 | nC |
| Q_{gd} | Gate-drain charge | | | 21.7 | | nC |

1. Pulsed: pulse duration=300 μs , duty cycle 1.5%

2. $C_{oss \text{ eq}}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}

Table 7. Source drain diode

| Symbol | Parameter | Test conditions | Min | Typ. | Max | Unit |
|-----------------|-------------------------------|--|-----|------|-----|---------------|
| I_{SD} | Source-drain current | | | | 3.5 | A |
| $I_{SDM}^{(1)}$ | Source-drain current (pulsed) | | | | 14 | A |
| $V_{SD}^{(2)}$ | Forward on voltage | $I_{SD}=3.5\text{ A}$, $V_{GS}=0$ | | | 1.6 | V |
| t_{rr} | Reverse recovery time | $I_{SD}=3.5\text{ A}$, $di/dt = 100\text{A}/\mu\text{s}$, $V_{DD}=30\text{ V}$ (see Figure 22) | | 605 | | ns |
| Q_{rr} | Reverse recovery charge | | | 3.09 | | μC |
| I_{RRM} | Reverse recovery current | | | 10.5 | | A |
| t_{rr} | Reverse recovery time | $I_{SD}=3.5\text{ A}$, $di/dt = 100\text{A}/\mu\text{s}$, $V_{DD}=35\text{ V}$, $T_j=150^\circ\text{C}$ (see Figure 22) | | 742 | | ns |
| Q_{rr} | Reverse recovery charge | | | 4.2 | | μC |
| I_{RRM} | Reverse recovery current | | | 11.2 | | A |

1. Pulse width limited by safe operating area
2. Pulsed: pulse duration=300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area for TO-220FP

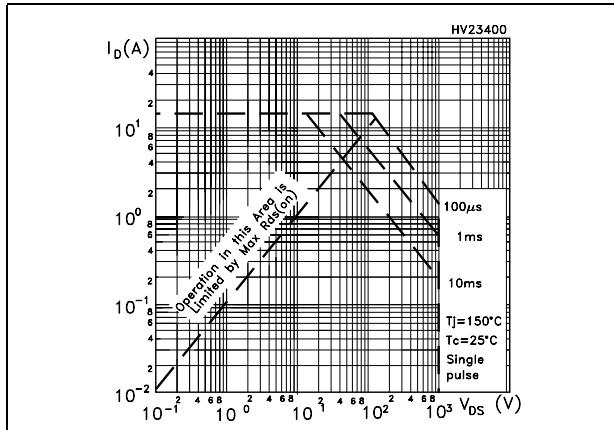


Figure 2. Thermal impedance for TO-220FP

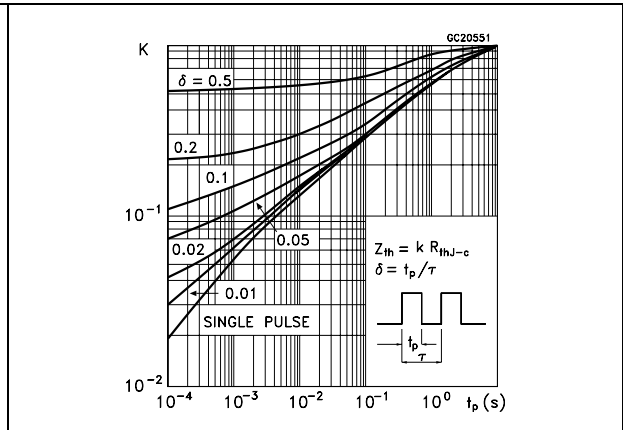


Figure 3. Safe operating area for TO-220

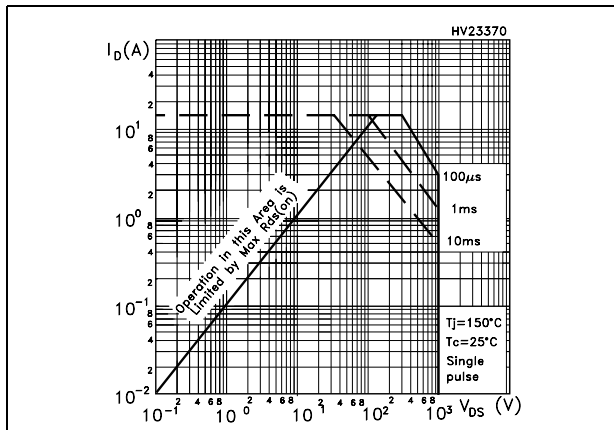


Figure 4. Thermal impedance for TO-220

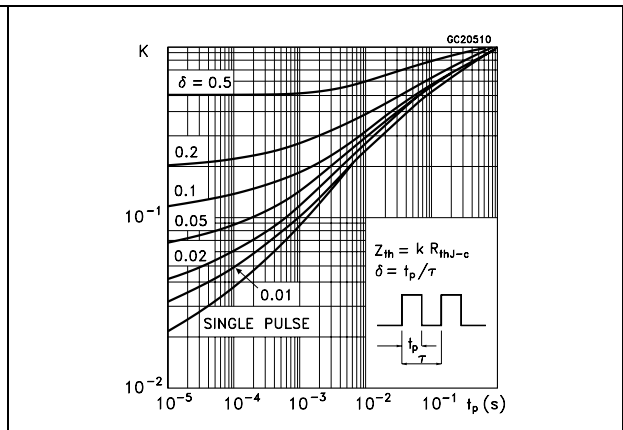


Figure 5. Safe operating area for TO-247

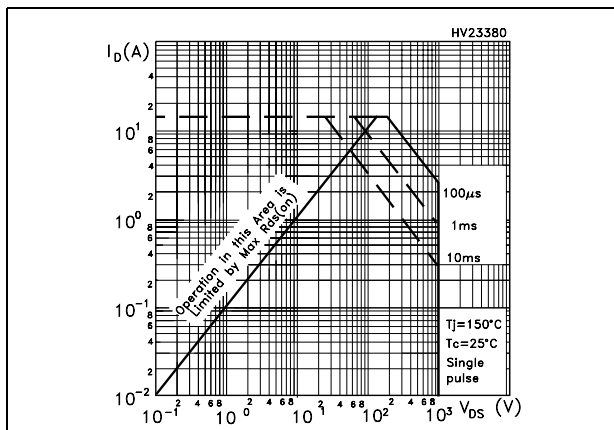


Figure 6. Thermal impedance for TO-247

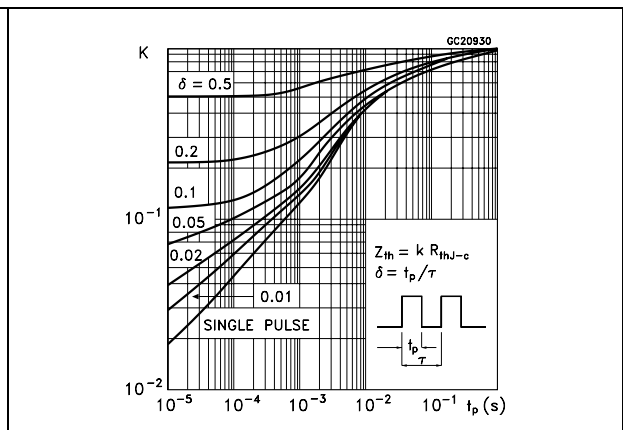


Figure 7. Output characteristics

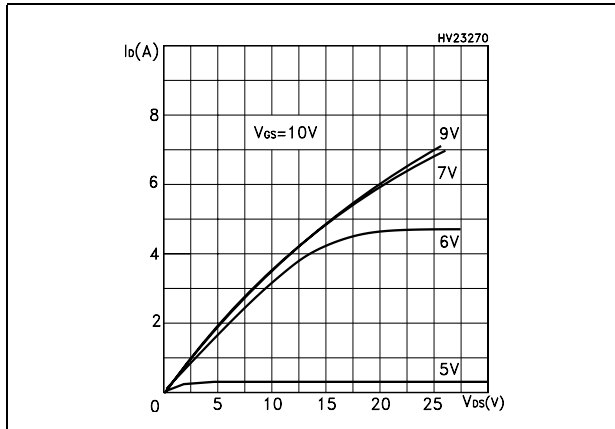


Figure 8. Transfer characteristics

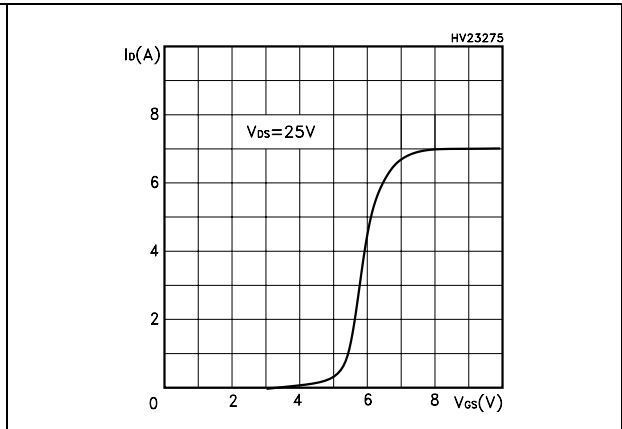


Figure 9. Transconductance

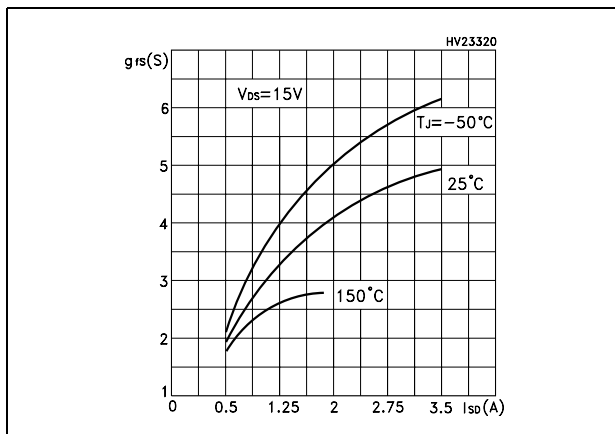


Figure 10. Static drain-source on resistance

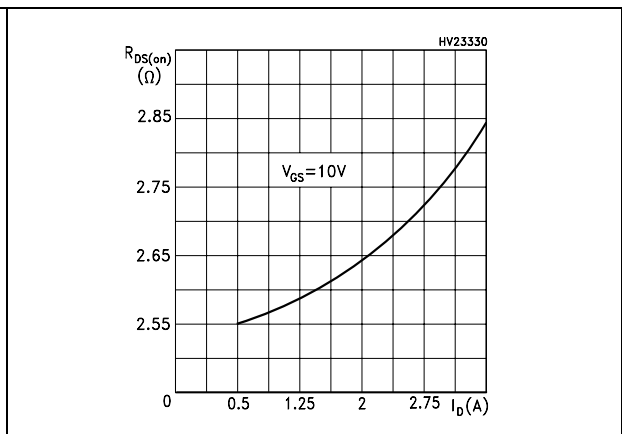


Figure 11. Gate charge vs gate-source voltage

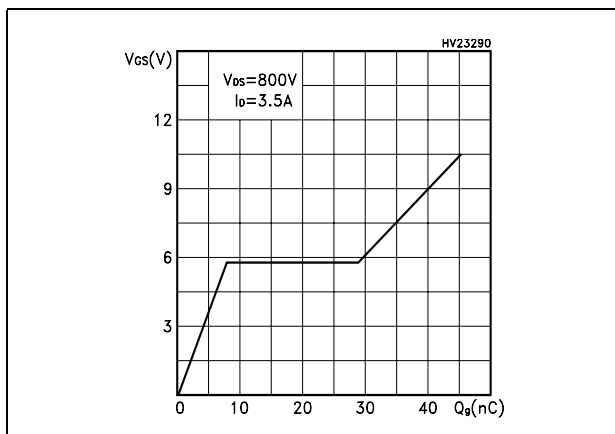


Figure 12. Capacitance variations

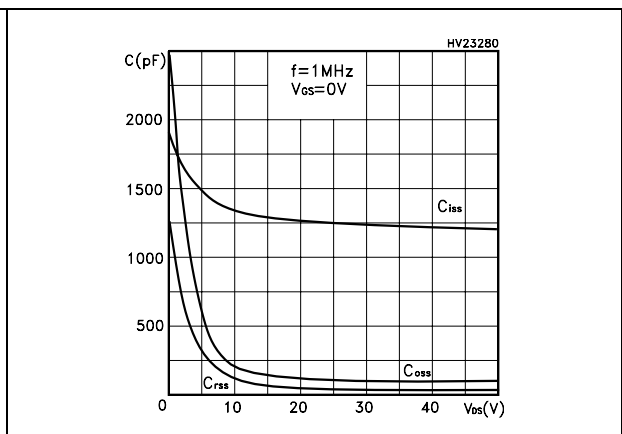


Figure 13. Normalized gate threshold voltage vs temperature

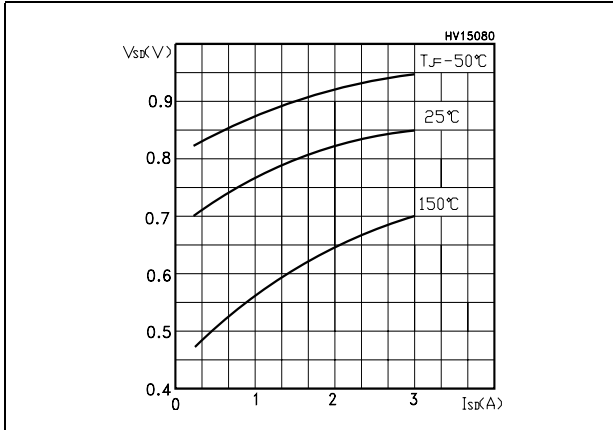


Figure 14. Normalized on resistance vs temperature

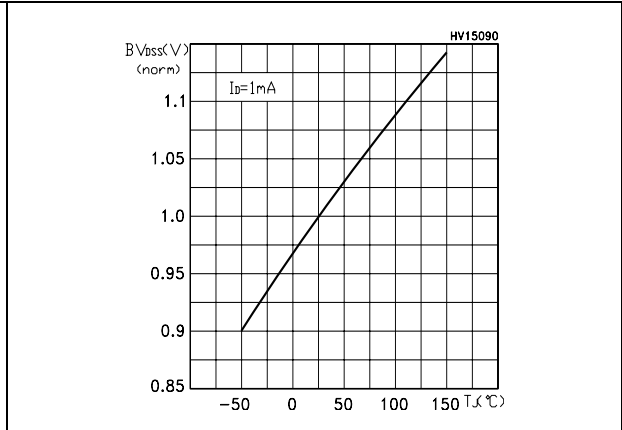


Figure 15. Source-drain diode forward characteristics

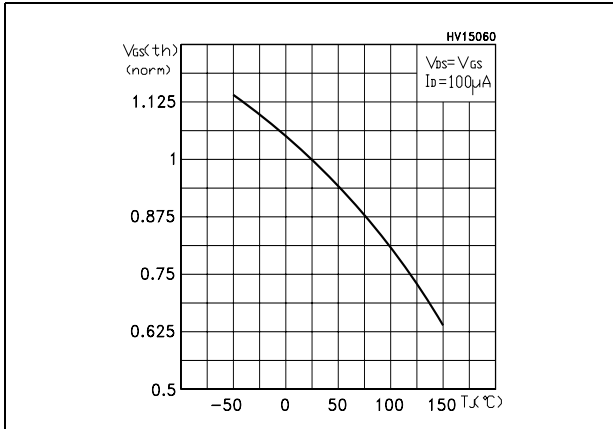


Figure 16. Normalized BVdss vs temperature

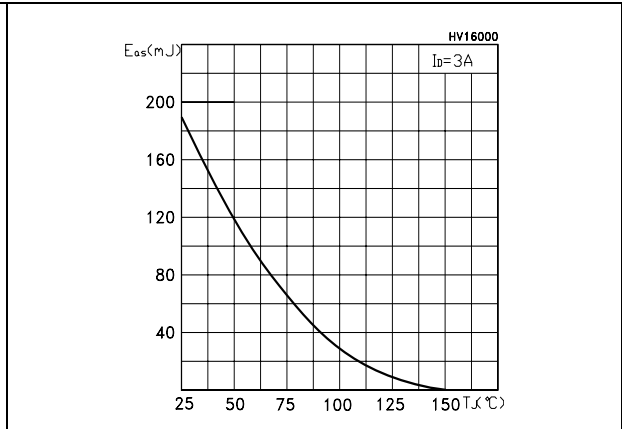
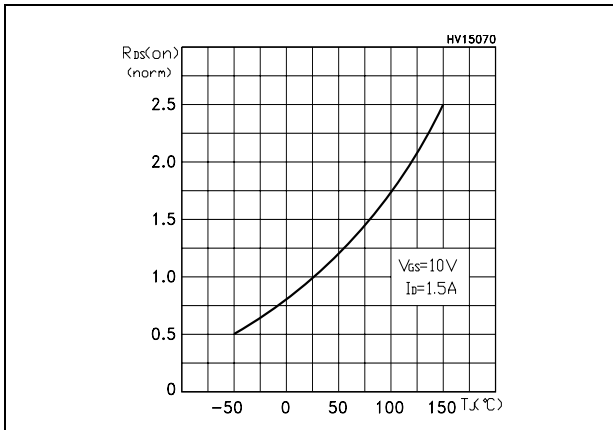


Figure 17. Maximum avalanche energy vs temperature



3 Test circuit

Figure 18. Unclamped Inductive load test circuit

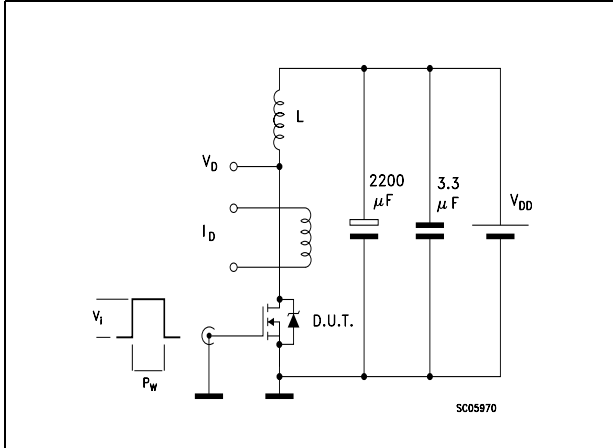


Figure 19. Unclamped Inductive waveform

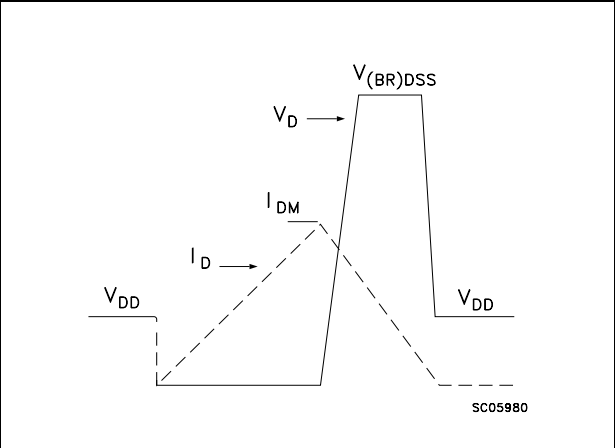


Figure 20. Switching times test circuit for resistive load

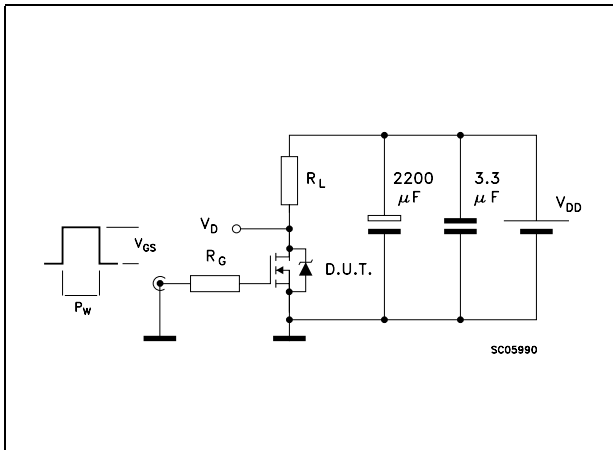


Figure 21. Gate charge test circuit

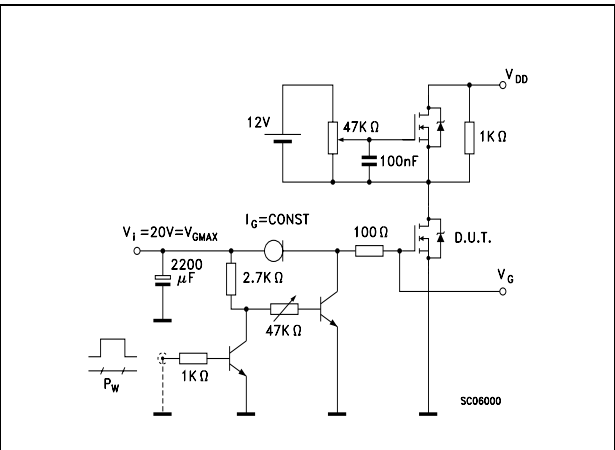
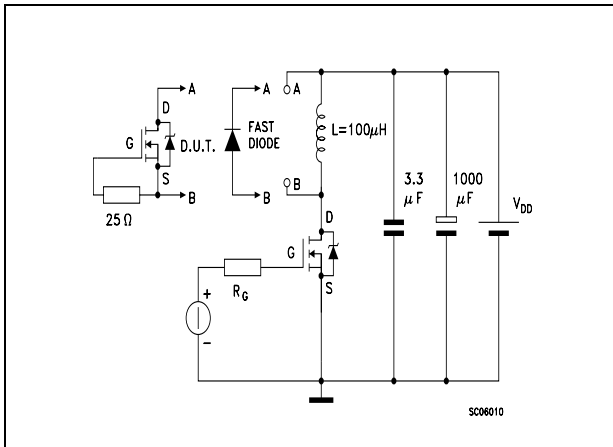


Figure 22. Test circuit for inductive load switching and diode recovery times

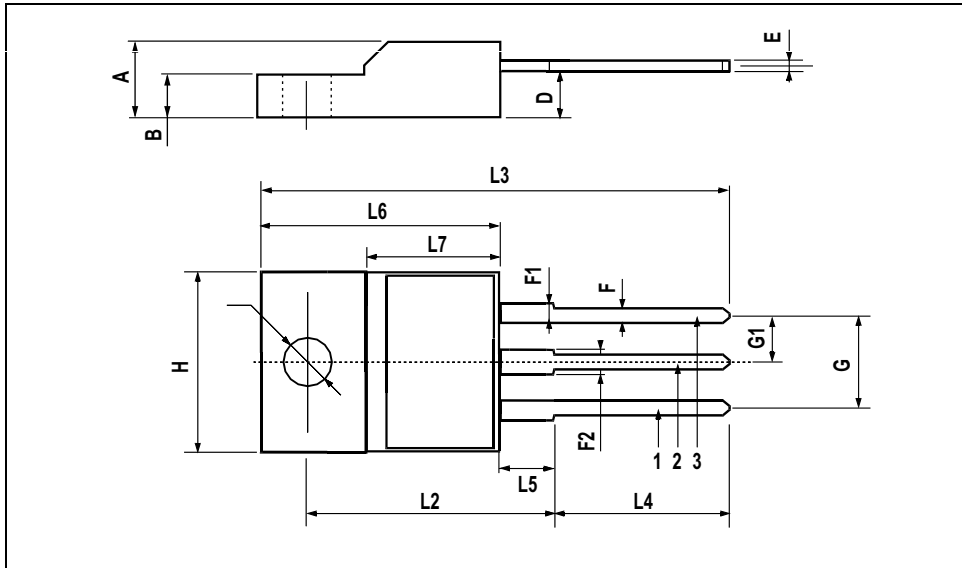


4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

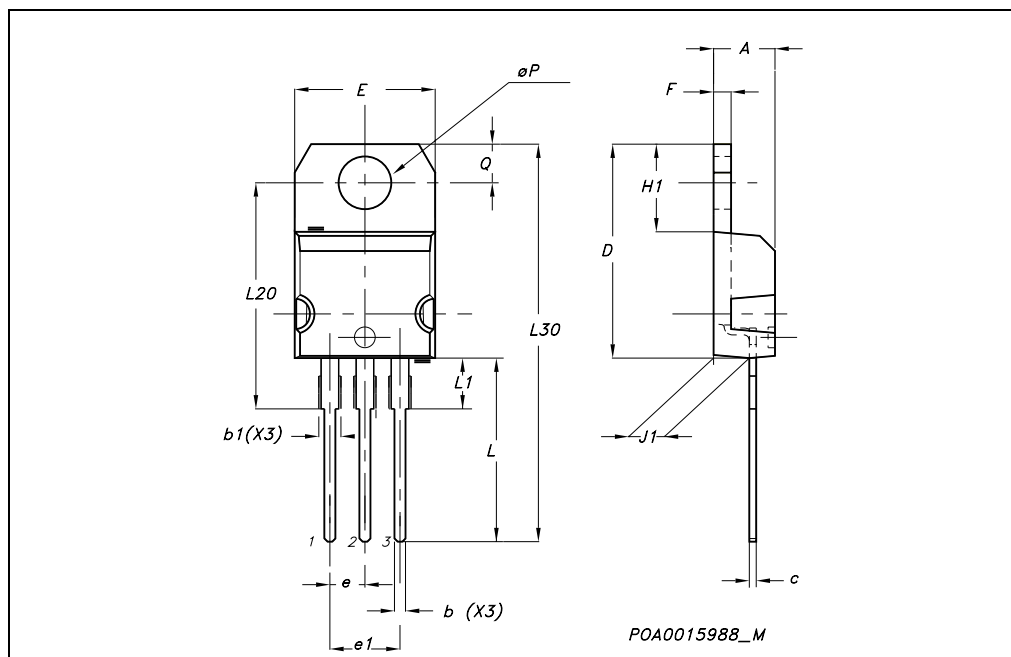
TO-220FP MECHANICAL DATA

| DIM. | mm. | | | inch | | |
|------|------|-----|------|-------|-------|-------|
| | MIN. | TYP | MAX. | MIN. | TYP. | MAX. |
| A | 4.4 | | 4.6 | 0.173 | | 0.181 |
| B | 2.5 | | 2.7 | 0.098 | | 0.106 |
| D | 2.5 | | 2.75 | 0.098 | | 0.108 |
| E | 0.45 | | 0.7 | 0.017 | | 0.027 |
| F | 0.75 | | 1 | 0.030 | | 0.039 |
| F1 | 1.15 | | 1.7 | 0.045 | | 0.067 |
| F2 | 1.15 | | 1.7 | 0.045 | | 0.067 |
| G | 4.95 | | 5.2 | 0.195 | | 0.204 |
| G1 | 2.4 | | 2.7 | 0.094 | | 0.106 |
| H | 10 | | 10.4 | 0.393 | | 0.409 |
| L2 | | 16 | | | 0.630 | |
| L3 | 28.6 | | 30.6 | 1.126 | | 1.204 |
| L4 | 9.8 | | 10.6 | .0385 | | 0.417 |
| L5 | 2.9 | | 3.6 | 0.114 | | 0.141 |
| L6 | 15.9 | | 16.4 | 0.626 | | 0.645 |
| L7 | 9 | | 9.3 | 0.354 | | 0.366 |
| Ø | 3 | | 3.2 | 0.118 | | 0.126 |



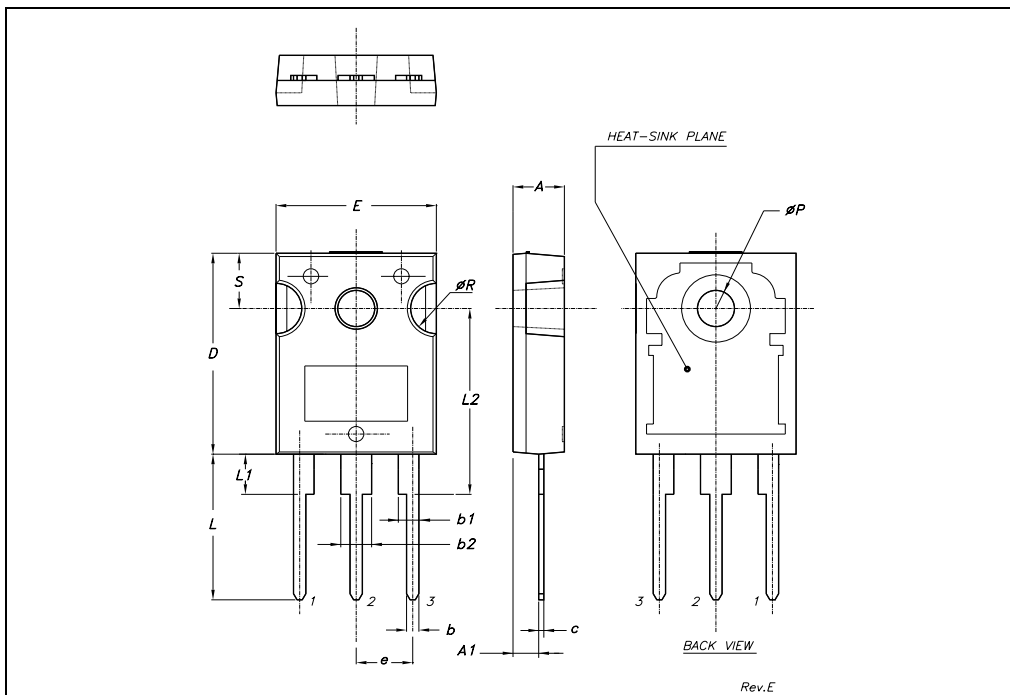
TO-220 MECHANICAL DATA

| DIM. | mm. | | | inch | | |
|------|-------|-------|-------|-------|-------|-------|
| | MIN. | TYP. | MAX. | MIN. | TYP. | MAX. |
| A | 4.40 | | 4.60 | 0.173 | | 0.181 |
| b | 0.61 | | 0.88 | 0.024 | | 0.034 |
| b1 | 1.15 | | 1.70 | 0.045 | | 0.066 |
| c | 0.49 | | 0.70 | 0.019 | | 0.027 |
| D | 15.25 | | 15.75 | 0.60 | | 0.620 |
| E | 10 | | 10.40 | 0.393 | | 0.409 |
| e | 2.40 | | 2.70 | 0.094 | | 0.106 |
| e1 | 4.95 | | 5.15 | 0.194 | | 0.202 |
| F | 1.23 | | 1.32 | 0.048 | | 0.052 |
| H1 | 6.20 | | 6.60 | 0.244 | | 0.256 |
| J1 | 2.40 | | 2.72 | 0.094 | | 0.107 |
| L | 13 | | 14 | 0.511 | | 0.551 |
| L1 | 3.50 | | 3.93 | 0.137 | | 0.154 |
| L20 | | 16.40 | | | 0.645 | |
| L30 | | 28.90 | | | 1.137 | |
| øP | 3.75 | | 3.85 | 0.147 | | 0.151 |
| Q | 2.65 | | 2.95 | 0.104 | | 0.116 |



TO-247 MECHANICAL DATA

| DIM. | mm. | | | inch | | |
|------|-------|-------|-------|-------|-------|-------|
| | MIN. | TYP. | MAX. | MIN. | TYP. | MAX. |
| A | 4.85 | | 5.15 | 0.19 | | 0.20 |
| A1 | 2.20 | | 2.60 | 0.086 | | 0.102 |
| b | 1.0 | | 1.40 | 0.039 | | 0.055 |
| b1 | 2.0 | | 2.40 | 0.079 | | 0.094 |
| b2 | 3.0 | | 3.40 | 0.118 | | 0.134 |
| c | 0.40 | | 0.80 | 0.015 | | 0.03 |
| D | 19.85 | | 20.15 | 0.781 | | 0.793 |
| E | 15.45 | | 15.75 | 0.608 | | 0.620 |
| e | | 5.45 | | | 0.214 | |
| L | 14.20 | | 14.80 | 0.560 | | 0.582 |
| L1 | 3.70 | | 4.30 | 0.14 | | 0.17 |
| L2 | | 18.50 | | | 0.728 | |
| øP | 3.55 | | 3.65 | 0.140 | | 0.143 |
| øR | 4.50 | | 5.50 | 0.177 | | 0.216 |
| S | | 5.50 | | | 0.216 | |



5 Revision history

Table 8. Revision history

| Date | Revision | Changes |
|-------------|-----------------|---------------------------------|
| 12-Oct-2004 | 1 | First release |
| 08-Sep-2005 | 2 | Complete datasheet |
| 16-Dec-2005 | 3 | Inserted ecopack indication |
| 16-Aug-2006 | 4 | New template, no content change |

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